## Application No. <u>09/497,508</u>

East Search 5/9/01

					017101
Search	L No.		iliext Search	S845777571579762	Data Bases
			("438/512,515,517,526,539,554,555,563	 W 1971	USPAT; EPO; JPO;
IS&R	Ll	1932	").CCLS.	5/9/01 8:41	Derwent; IBM TDB
			,	 -	USPAT; EPO; JPO;
BRS	L2	314	l and polycrystalline	5/9/01 8:42	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L3	44	2 and amorphous adj silicon	5/9/01 8:43	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L6	6	3 and (ni nickel)	5/9/01 8:46	Derwent; IBM TDB
	,				

Search Result

USPAT	Date	Page	Title Comment	@Cl/Sub.	Cl/Sub	Inventor
			Implantation method having improved			3.50
US 5354697 A	19941011	9	material purity	438/514	438/526 ; 438/531	Oostra, Doeke J., et al.
			Methods for forming epitaxial self-			
			aligned calcium silicide contacts and			
US 5248633 A	19930928	7	structures	438/526	438/533	Morar, John F., et al.
	·					OKABAYASHI,
			METHOD FOR FORMING	ļ	•	HIDEKAZU , SAITO,
JP 02137326 A	19900525	2	MICROSCOPIC STRUCTURE	<u> </u>	438/512	SHUICHI, et al.
				ļ		
,						
ļ				ļ		
				<u> </u>		· · · · · · · · · · · · · · · · · · ·
			•			l



East Search

5/9/01

Search	LNo	Hits	itext Search			
						USPAT; EPO; JPO;
BRS	LI	31644	thin adj film adj transistor or tft		5/9/01 9:53	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L2	227	1 and solar adj cell		5/9/01 9:54	
						USPAT; EPO; JPO;
BRS	L4	51	2 and (ni nickel)		5/9/01 9:55	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L5	10	4 and amorphous adj silicon adj film		5/9/01 9:56	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L6	5 ·	5 and polycrystalline	<u> </u>	5/9/01 9:57	Derwent; IBM TDB

## Search Result

USPAT	Date .	Rage	Title	<b>©</b> Cl/Sub	Cl/Sub	Inventor.
			Polycrystalline silicon semiconductor			
			having an amorphous silicon buffer		257/431; 257/461;	
US 5667597 A	19970916	15	layer	136/258	257/49	Ishihara, Shunichi
			Method for forming single silicon		117/45 ; 117/902 ;	
US 5893948 A	19990413	13	crystals using nucleation sites	117/43	117/933	Nickel, Norbert H., et al.
			Method and apparatus for continuously			
			forming functional deposited films		118/718;	
			with a large area by a microwave plasma		118/723ME ;	
US 5527391 A	19960618	- 68	CVD method	118/719	118/723MW	Echizen, Hiroshi, et al.
	·		Apparatus for continuously forming a		118/723ME ;	
			large area functional deposit film	j	118/725 ; 118/730 ;	
1			including microwave transmissive		118/733 ; 136/249 ;	·
US 5296036 A	19940322	59	member transfer mean	118/718	136/258 ; 156/345	Matsuyama, Jinsho, et al.
			Method for continuously forming			
	-		functional deposited films with a large		136/258 ; 427/248.1	
			area by a microwave plasma CVD		; 427/314 ;	
US 5114770 A	19920519	69	method	427/575	427/398.1	Echizen, Hiroshi, et al.
		9				

East Search

Search	L No.	Hits Text Search	rackig korsaki i so ikisi	Data Bases
		(("5677549") or ("5656825") or		
	l	("5646424") or ("5744824") or		
		("5705829") or ("5700333") or		USPAT; EPO; JPO
IS&R	7	("5696388")).PN.	5/9/01 10:28	Derwent; IBM TDE
		(("5624851") or ("5620910") or		USPAT; EPO; JPO
IS&R	4	("5616506") or ("5614733")).PN.	5/9/01 10:40	Derwent; IBM TDE
'		(("5508533") or ("5501989") or		<u> </u>
		("5654203") or ("5663077") or		
		("5643826") or ("5543352") or		
		("5426064") or ("5481121") or		
		("5488000") or ("5492843") or	ì	USPAT; EPO; JPO
IS&R	11	("5534716")).PN.	5/9/01 10:50	Derwent; IBM TDE
		(("5595923") or ("5589694") or		Ť í
		("5569610") or ("5580792") or	İ	
		("5606179") or ("5605846") or		·
	i	("5604360") or ("5595944") or	Y.	USPAT; EPO; JPO
IS&R	9	("5612250")).PN.	5/9/01 11:04	Derwent; IBM TDB
	,			
				1

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
	ļ	ļ				
		ļ	·			
		-				
<del>,</del>		<u> </u>				
			····-			
					*	
	· · · · · · · · · · · · · · · · · · ·	<b></b>	-			<del></del>
,						
· · · · · · · · · · · · · · · · · · ·						